Discrete POWER & Signal **Technologies**

MPS6531

FAIRCHILD SEMICONDUCTOR TM

MPS6531



NPN General Purpose Amplifier

This device is designed for use as a medium power amplifier and switch requiring collector currents to 500 mA. Sourced from Process 19. See PN2222A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted					
Symbol	Characteristic	Мах	Units		
		MPS6531			
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C		
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	83.3	°C/W		
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W		

NPN General Purpose Amplifier (continued)

HubbleDefinitionDefinitionDefinitionHubbleHubbleHubble $V_{(BR)CBO}$ Collector-Base Breakdown Voltage $I_c = 10 \ \mu A, I_E = 0$ 60V $V_{(BR)EBO}$ Emitter-Base Breakdown Voltage $I_E = 10 \ \mu A, I_C = 0$ 5.0V I_{CBO} Collector Cutoff Current $V_{CB} = 40 \ V, I_E = 0$ $V_{CB} = 40 \ V, I_E = 0, T_A = 60 \ ^\circ C$ 50nON CHARACTERISTICS*NFEDC Current Gain $V_{CE} = 1.0 \ V, I_C = 10 \ mA$ $V_{CE} = 1.0 \ V, I_C = 500 \ mA$ 60 90 50 VCE(sat)Collector-Emitter Saturation Voltage $I_C = 100 \ mA, I_B = 10 \ mA$ 0.3 $V_{BE(sat)}$ Base-Emitter Saturation Voltage $I_C = 100 \ mA, I_B = 10 \ mA$ 1.0	Collector-Emitter Breakdown Voltage* $I_c = 10 \text{ mA}, I_B = 0$ 40VCollector-Base Breakdown Voltage $I_c = 10 \mu A, I_E = 0$ 60VEmitter-Base Breakdown Voltage $I_E = 10 \mu A, I_C = 0$ 5.0V
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$V_{BE(sat)}$ Base-Emitter Saturation Voltage I _c = 100 mA, I _B = 10 mA 1.0 V	Collector-Emitter Saturation Voltage $I_c = 100 \text{ mA}$ $I_B = 10 \text{ mA}$ 0.3 V
	Base-Emitter Saturation Voltage $I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$ 1.0 V
SMALL SIGNAL CHARACTERISTICS	
	NAL CHARACTERISTICS
C_{ob} Output Capacitance $V_{CB} = 10 V$, f = 100 kHz 5.0 p	Dutput Capacitance $V_{CB} = 10 \text{ V}, \text{ f} = 100 \text{ kHz}$ 5.0 pl
*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%	

MPS6531



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